



JA00200100P52FS; 20 - 100 MHz 150W Amplifier

- Solid-state Class AB design
- Ruggedized MOS Transistors
- MOS Transistors
- High reliability and ruggedness
- Ultra Small Dimensions & Ultra Light Weight
- Forward/Reflected Power Monitorings
- Temperature and Current Monitorings
- Enable Control



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	20-100 MHz
Output Power:	150 W CW
Nominal Gain:	52 dB
Gain Flatness:	± 2 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 for 1 min.
DC Supply Voltage:	28 VDC
DC Current:	15 A
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F/G
Vibration:	MIL-STD-810F/G

INTERFACES

RF Input:	SMA Female
RF Output:	N Female
7W2 COMBO:	1) Enable (Act. Low)
	2) GND
	3) Temp.*
	4) Fwd. Power
	5) Rev. Power
	A1) GND
	A2) 28 VDC

*Temp(°C) = (Voltage(mV) - 1000) / 20

MECHANICAL SPECIFICATIONS

Size (mm) :	97 × 194 × 24
Weight :	600 gr.
Plating :	Yellow Chromate

